

steven Denbaars

List of Publications by Year in descending order

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1,025
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54,430
citations

1043

113
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2743

192
g-index

1040
all docs

1040
docs citations

1040
times ranked

17734
citing authors

#	ARTICLE	IF	CITATIONS
1	Prospects for LED lighting. Nature Photonics, 2009, 3, 180-182.	15.6	1,847
2	Direct formation of quantum-sized dots from uniform coherent islands of InGaAs on GaAs surfaces. Applied Physics Letters, 1993, 63, 3203-3205.	1.5	1,697
3	Increase in the extraction efficiency of GaN-based light-emitting diodes via surface roughening. Applied Physics Letters, 2004, 84, 855-857.	1.5	1,239
4	Polarization effects, surface states, and the source of electrons in AlGaIn/GaN heterostructure field effect transistors. Applied Physics Letters, 2000, 77, 250-252.	1.5	948
5	Role of threading dislocation structure on the x-ray diffraction peak widths in epitaxial GaN films. Applied Physics Letters, 1996, 68, 643-645.	1.5	781
6	Absorption coefficient, energy gap, exciton binding energy, and recombination lifetime of GaN obtained from transmission measurements. Applied Physics Letters, 1997, 71, 2572-2574.	1.5	654
7	S-shaped temperature-dependent emission shift and carrier dynamics in InGaIn/GaN multiple quantum wells. Applied Physics Letters, 1998, 73, 1370-1372.	1.5	654
8	Origin of defect-insensitive emission probability in In-containing (Al,In,Ga)N alloy semiconductors. Nature Materials, 2006, 5, 810-816.	13.3	625
9	Structural characterization of nonpolar (112̄,0) a-plane GaN thin films grown on (11̄,02) r-plane sapphire. Applied Physics Letters, 2002, 81, 469-471.	1.5	484
10	Effective band gap inhomogeneity and piezoelectric field in InGaIn/GaN multiquantum well structures. Applied Physics Letters, 1998, 73, 2006-2008.	1.5	427
11	Structural origin of V-defects and correlation with localized excitonic centers in InGaIn/GaN multiple quantum wells. Applied Physics Letters, 1998, 72, 692-694.	1.5	417
12	High-power AlGaIn/GaN HEMTs for Ka-band applications. IEEE Electron Device Letters, 2005, 26, 781-783.	2.2	408
13	Defect structure of metal-organic chemical vapor deposition-grown epitaxial (0001) GaN/Al ₂ O ₃ . Journal of Applied Physics, 1996, 80, 3228-3237.	1.1	403
14	AlGaIn/AlN/GaN high-power microwave HEMT. IEEE Electron Device Letters, 2001, 22, 457-459.	2.2	403
15	High quantum efficiency InGaIn/GaN solar cells with 2.95 eV band gap. Applied Physics Letters, 2008, 93, .	1.5	400
16	Homoepitaxial growth of GaN under Ga-stable and N-stable conditions by plasma-assisted molecular beam epitaxy. Journal of Applied Physics, 1997, 82, 5472-5479.	1.1	387
17	Polarization-induced charge and electron mobility in AlGaIn/GaN heterostructures grown by plasma-assisted molecular-beam epitaxy. Journal of Applied Physics, 1999, 86, 4520-4526.	1.1	380
18	Dislocation mediated surface morphology of GaN. Journal of Applied Physics, 1999, 85, 6470-6476.	1.1	371

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19	High Breakdown Voltage Achieved on AlGa _N /Ga _N HEMTs With Integrated Slant Field Plates. IEEE Electron Device Letters, 2006, 27, 713-715.	2.2	367
20	Heavy doping effects in Mg-doped Ga _N . Journal of Applied Physics, 2000, 87, 1832-1835.	1.1	355
21	Development of gallium-nitride-based light-emitting diodes (LEDs) and laser diodes for energy-efficient lighting and displays. Acta Materialia, 2013, 61, 945-951.	3.8	352
22	Very high breakdown voltage and large transconductance realized on Ga _N heterojunction field effect transistors. Applied Physics Letters, 1996, 69, 1438-1440.	1.5	339
23	Electrical characterization of Ga _N p-n junctions with and without threading dislocations. Applied Physics Letters, 1998, 73, 975-977.	1.5	339
24	Growth of Fe doped semi-insulating Ga _N by metalorganic chemical vapor deposition. Applied Physics Letters, 2002, 81, 439-441.	1.5	326
25	Consequences of Optimal Bond Valence on Structural Rigidity and Improved Luminescence Properties in Sr ₂ Ba ₂ SiO ₄ :Eu ²⁺ Orthosilicate Phosphors. Chemistry of Materials, 2014, 26, 2275-2282.	3.2	323
26	Semipolar $\text{InGa}_x\text{N}_{1-x}$ InGa _N /Ga _N Light-Emitting Diodes for High-Efficiency Solid-State Lighting. Journal of Display Technology, 2013, 9, 190-198.	1.3	316
27	Structural evolution in epitaxial metalorganic chemical vapor deposition grown Ga _N films on sapphire. Applied Physics Letters, 1995, 67, 1541-1543.	1.5	311
28	High-performance (Al,Ga) _N -based solar-blind ultraviolet detectors on laterally epitaxially overgrown Ga _N . Applied Physics Letters, 1999, 75, 247-249.	1.5	311
29	Efficient and Color-Tunable Oxyfluoride Solid Solution Phosphors for Solid-State White Lighting. Advanced Materials, 2011, 23, 2300-2305.	11.1	311
30	Coupling of InGa _N quantum-well photoluminescence to silver surface plasmons. Physical Review B, 1999, 60, 11564-11567.	1.1	308
31	Al _N /Ga _N and (Al,Ga) _N /Al _N /Ga _N two-dimensional electron gas structures grown by plasma-assisted molecular-beam epitaxy. Journal of Applied Physics, 2001, 90, 5196-5201.	1.1	280
32	High breakdown Ga _N HEMT with overlapping gate structure. IEEE Electron Device Letters, 2000, 21, 421-423.	2.2	264
33	Influence of sapphire nitridation on properties of gallium nitride grown by metalorganic chemical vapor deposition. Applied Physics Letters, 1996, 68, 1525-1527.	1.5	261
34	High Al-content AlGa _N /Ga _N MODFETs for ultrahigh performance. IEEE Electron Device Letters, 1998, 19, 50-53.	2.2	260
35	Enhanced Mg doping efficiency in Al _{0.2} Ga _{0.8} N/Ga _N superlattices. Applied Physics Letters, 1999, 74, 3681-3683.	1.5	257
36	Materials and growth issues for high-performance nonpolar and semipolar light-emitting devices. Semiconductor Science and Technology, 2012, 27, 024001.	1.0	253

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37	Scanning capacitance microscopy imaging of threading dislocations in GaN films grown on (0001) sapphire by metalorganic chemical vapor deposition. Applied Physics Letters, 1998, 72, 2247-2249.	1.5	251
38	High Power and High External Efficiency m-Plane InGaN Light Emitting Diodes. Japanese Journal of Applied Physics, 2007, 46, L126-L128.	0.8	241
39	Nonpolar and Semipolar III-Nitride Light-Emitting Diodes: Achievements and Challenges. IEEE Transactions on Electron Devices, 2010, 57, 88-100.	1.6	230
40	Nucleation layer evolution in metalorganic chemical vapor deposition grown GaN. Applied Physics Letters, 1996, 68, 1371-1373.	1.5	228
41	Microstructure of GaN laterally overgrown by metalorganic chemical vapor deposition. Applied Physics Letters, 1998, 73, 747-749.	1.5	228
42	$\text{Sr}_{2.975}\text{Ba}_{0.025}\text{AlO}_4\text{F}$: a Highly Efficient Green-Emitting Oxyfluoride Phosphor for Solid State White Lighting. Chemistry of Materials, 2010, 22, 2842-2849.	3.2	227
43	Indium tin oxide contacts to gallium nitride optoelectronic devices. Applied Physics Letters, 1999, 74, 3930-3932.	1.5	226
44	Demonstration of a semipolar (101 $\bar{1}$ 3 $\bar{1}$) InGaN/GaN green light emitting diode. Applied Physics Letters, 2005, 87, 231110.	1.5	220
45	High-brightness polarized light-emitting diodes. Light: Science and Applications, 2012, 1, e22-e22.	7.7	217
46	High efficiency of III-nitride micro-light-emitting diodes by sidewall passivation using atomic layer deposition. Optics Express, 2018, 26, 21324.	1.7	213
47	GaN microwave electronics. IEEE Transactions on Microwave Theory and Techniques, 1998, 46, 756-761.	2.9	210
48	Demonstration of Nonpolar m-Plane InGaN/GaN Laser Diodes. Japanese Journal of Applied Physics, 2007, 46, L190-L191.	0.8	204
49	Robust thermal performance of $\text{Sr}_2\text{Si}_5\text{N}_8\text{:Eu}^{2+}$: An efficient red emitting phosphor for light emitting diode based white lighting. Applied Physics Letters, 2011, 99, .	1.5	202
50	Demonstration of Nonpolar m-Plane InGaN/GaN Light-Emitting Diodes on Free-Standing m-Plane GaN Substrates. Japanese Journal of Applied Physics, 2005, 44, L173-L175.	0.8	200
51	Nonpolar InGaN/GaN emitters on reduced-defect lateral epitaxially overgrown a-plane GaN with drive-current-independent electroluminescence emission peak. Applied Physics Letters, 2004, 85, 5143-5145.	1.5	199
52	AlGaIn/GaN current aperture vertical electron transistors with regrown channels. Journal of Applied Physics, 2004, 95, 2073-2078.	1.1	197
53	High internal and external quantum efficiency InGaIn/GaN solar cells. Applied Physics Letters, 2011, 98, .	1.5	195
54	Crystallographic orientation dependence of dopant and impurity incorporation in GaN films grown by metalorganic chemical vapor deposition. Journal of Crystal Growth, 2009, 311, 3817-3823.	0.7	192

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55	Spin coherence and dephasing in GaN. Physical Review B, 2001, 63, .	1.1	190
56	Photonic-crystal GaN light-emitting diodes with tailored guided modes distribution. Applied Physics Letters, 2006, 88, 061124.	1.5	189
57	Polarization effects in AlGaIn/GaN and GaN/AlGaIn/GaN heterostructures. Journal of Applied Physics, 2003, 93, 10114-10118.	1.1	188
58	White light from InGaIn/conjugated polymer hybrid light-emitting diodes. Applied Physics Letters, 1997, 70, 2664-2666.	1.5	186
59	Measurement of electron overflow in 450 nm InGaIn light-emitting diode structures. Applied Physics Letters, 2009, 94, 061116.	1.5	181
60	LaSr ₂ AlO ₅ , a Versatile Host Compound for Ce ³⁺ -Based Yellow Phosphors: Structural Tuning of Optical Properties and Use in Solid-State White Lighting. Chemistry of Materials, 2009, 21, 2957-2966.	3.2	180
61	Metalorganic chemical vapor deposition of GaN on Si(111): Stress control and application to field-effect transistors. Journal of Applied Physics, 2001, 89, 7846-7851.	1.1	178
62	High-Power Blue-Violet Semipolar (200) InGaIn/GaN Light-Emitting Diodes with Low Efficiency Droop at 200 A/cm ² . Applied Physics Express, 2011, 4, 082104.	1.1	177
63	Defect reduction in (112̄,0) a-plane gallium nitride via lateral epitaxial overgrowth by hydride vapor-phase epitaxy. Applied Physics Letters, 2003, 83, 644-646.	1.5	176
64	Proxies from Ab Initio Calculations for Screening Efficient Ce ³⁺ Phosphor Hosts. Journal of Physical Chemistry C, 2013, 117, 17955-17959.	1.5	176
65	Influence of the Dynamic Access Resistance in the g_m and f_T Linearity of AlGaIn/GaN HEMTs. IEEE Transactions on Electron Devices, 2005, 52, 2117-2123.	1.6	174
66	N-polar GaIn epitaxy and high electron mobility transistors. Semiconductor Science and Technology, 2013, 28, 074009.	1.0	172
67	Threading dislocation reduction via laterally overgrown nonpolar (112̄,0)a-plane GaIn. Applied Physics Letters, 2002, 81, 1201-1203.	1.5	169
68	Sustained high external quantum efficiency in ultrasmall blue InGaN nitride micro-LEDs. Applied Physics Express, 2017, 10, 032101.	1.1	169
69	Indium incorporation and emission properties of nonpolar and semipolar InGaIn quantum wells. Applied Physics Letters, 2012, 100, .	1.5	168
70	Low interface trap density for remote plasma deposited SiO ₂ on n-type GaIn. Applied Physics Letters, 1996, 68, 1850-1852.	1.5	167
71	Optical properties of yellow light-emitting diodes grown on semipolar (112̂ ²) bulk GaIn substrates. Applied Physics Letters, 2008, 92, .	1.5	167
72	Optical properties of InGaIn quantum wells. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1999, 59, 298-306.	1.7	164

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73	Impact of carbon on trap states in n-type GaN grown by metalorganic chemical vapor deposition. Applied Physics Letters, 2004, 84, 374-376.	1.5	164
74	Realization of wide electron slabs by polarization bulk doping in graded III-V nitride semiconductor alloys. Applied Physics Letters, 2002, 81, 4395-4397.	1.5	163
75	Recent progress in metal-organic chemical vapor deposition of $\left(\text{000} \right) \text{N-polar}$ group-III nitrides. Semiconductor Science and Technology, 2014, 29, 113001.	1.0	163
76	Metalorganic chemical vapor deposition of high mobility AlGaIn/GaN heterostructures. Journal of Applied Physics, 1999, 86, 5850-5857.	1.1	161
77	High-Efficiency Single-Quantum-Well Green and Yellow-Green Light-Emitting Diodes on Semipolar (20 $\bar{1}$ 1) GaN Substrates. Applied Physics Express, 2010, 3, 122102.	1.1	161
78	Bias dependent microwave performance of AlGaIn/GaN MODFET's up to 100 V. IEEE Electron Device Letters, 1997, 18, 290-292.	2.2	160
79	Influence of the substrate misorientation on the properties of N-polar GaN films grown by metal organic chemical vapor deposition. Journal of Applied Physics, 2007, 102, 083546.	1.1	160
80	Emission mechanisms of bulk GaN and InGaIn quantum wells prepared by lateral epitaxial overgrowth. Applied Physics Letters, 1999, 74, 1460-1462.	1.5	158
81	Memory Effect and Redistribution of Mg into Sequentially Regrown GaN Layer by Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2003, 42, 50-53.	0.8	158
82	A yellow-emitting Ce ³⁺ phosphor, La _{1-x} Ce _x Sr ₂ AlO ₅ , for white light-emitting diodes. Applied Physics Letters, 2008, 93, .	1.5	158
83	Photonic bands in two-dimensionally patterned multimode GaN waveguides for light extraction. Applied Physics Letters, 2005, 87, 101107.	1.5	154
84	High luminous flux from single crystal phosphor-converted laser-based white lighting system. Optics Express, 2016, 24, A215.	1.7	153
85	High-performance E-mode AlGaIn/GaN HEMTs. IEEE Electron Device Letters, 2006, 27, 428-430.	2.2	152
86	Structural and morphological characteristics of planar (112 $\bar{1}$,0) a-plane gallium nitride grown by hydride vapor phase epitaxy. Applied Physics Letters, 2003, 83, 1554-1556.	1.5	151
87	Efficient and stable laser-driven white lighting. AIP Advances, 2013, 3, .	0.6	151
88	Polarization-enhanced Mg doping of AlGaIn/GaN superlattices. Applied Physics Letters, 1999, 75, 2444-2446.	1.5	149
89	Advances in the LED Materials and Architectures for Energy-Saving Solid-State Lighting Toward "Lighting Revolution". IEEE Photonics Journal, 2012, 4, 613-619.	1.0	145
90	Improved electroluminescence on nonpolar m-plane InGaIn/GaN quantum wells LEDs. Physica Status Solidi - Rapid Research Letters, 2007, 1, 125-127.	1.2	144

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91	Impurity incorporation in heteroepitaxial N-face and Ga-face GaN films grown by metalorganic chemical vapor deposition. <i>Journal of Crystal Growth</i> , 2008, 310, 1124-1131.	0.7	144
92	Comparison of size-dependent characteristics of blue and green InGaN microLEDs down to 1 μm in diameter. <i>Applied Physics Letters</i> , 2020, 116, .	1.5	141
93	Defect reduction in (11 $\bar{2}$ 00) m-plane gallium nitride via lateral epitaxial overgrowth by hydride vapor phase epitaxy. <i>Applied Physics Letters</i> , 2005, 86, 111917.	1.5	139
94	Limiting factors of room-temperature nonradiative photoluminescence lifetime in polar and nonpolar GaN studied by time-resolved photoluminescence and slow positron annihilation techniques. <i>Applied Physics Letters</i> , 2005, 86, 021914.	1.5	138
95	Measured and calculated radiative lifetime and optical absorption of $\text{In}_x\text{Ga}_{1-x}\text{N}/\text{GaN}$ quantum structures. <i>Physical Review B</i> , 2000, 61, 10994-11008.	1.1	137
96	Measured microwave power performance of AlGaIn/GaN MODFET. <i>IEEE Electron Device Letters</i> , 1996, 17, 455-457.	2.2	132
97	Size-independent peak efficiency of III-nitride micro-light-emitting-diodes using chemical treatment and sidewall passivation. <i>Applied Physics Express</i> , 2019, 12, 097004.	1.1	132
98	Si doping effect on strain reduction in compressively strained $\text{Al}_{0.49}\text{Ga}_{0.51}\text{N}$ thin films. <i>Applied Physics Letters</i> , 2003, 83, 674-676.	1.5	131
99	Microstructural evolution of a-plane GaN grown on a-plane SiC by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , 2004, 84, 1281-1283.	1.5	131
100	Group III-nitride lasers: a materials perspective. <i>Materials Today</i> , 2011, 14, 408-415.	8.3	129
101	Optically and thermally detected deep levels in n-type Schottky and p+n GaN diodes. <i>Applied Physics Letters</i> , 2000, 76, 3064-3066.	1.5	127
102	SIMS investigations into the effect of growth conditions on residual impurity and silicon incorporation in GaN and $\text{Al}_x\text{Ga}_{1-x}\text{N}$. <i>Journal of Electronic Materials</i> , 2000, 29, 15-20.	1.0	125
103	Photonic crystal laser lift-off GaN light-emitting diodes. <i>Applied Physics Letters</i> , 2006, 88, 133514.	1.5	124
104	Improved quality (11 $\bar{2}$ 0) a-plane GaN with sidewall lateral epitaxial overgrowth. <i>Applied Physics Letters</i> , 2006, 88, 061908.	1.5	123
105	High quantum efficiency InGaIn/GaN multiple quantum well solar cells with spectral response extending out to 520 nm. <i>Applied Physics Letters</i> , 2011, 98, .	1.5	122
106	Demonstration of a III-nitride vertical-cavity surface-emitting laser with a III-nitride tunnel junction intracavity contact. <i>Applied Physics Letters</i> , 2015, 107, .	1.5	122
107	Stable, Heat-Conducting Phosphor Composites for High-Power Laser Lighting. <i>ACS Applied Materials & Interfaces</i> , 2018, 10, 5673-5681.	4.0	121
108	Hydrogen passivation of deep levels in $\text{n}^+\text{-GaN}$. <i>Applied Physics Letters</i> , 2000, 77, 1499-1501.	1.5	120

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109	Growth and characterization of N-polar InGa N_{1-x} GaN multiquantum wells. Applied Physics Letters, 2007, 90, 191908.	1.5	118
110	Phosphorous Diffuser Diverged Blue Laser Diode for Indoor Lighting and Communication. Scientific Reports, 2015, 5, 18690.	1.6	118
111	Well-width dependence of photoluminescence emission from a-plane GaN/AlGaN multiple quantum wells. Applied Physics Letters, 2004, 84, 496-498.	1.5	117
112	4 Gbps direct modulation of 450 nm GaN laser for high-speed visible light communication. Optics Express, 2015, 23, 16232.	1.7	117
113	Role of inclined threading dislocations in stress relaxation in mismatched layers. Journal of Applied Physics, 2005, 97, 103534.	1.1	115
114	Mg doping of GaN layers grown by plasma-assisted molecular-beam epitaxy. Applied Physics Letters, 2000, 76, 718-720.	1.5	113
115	Review "Progress in High Performance III-Nitride Micro-Light-Emitting Diodes. ECS Journal of Solid State Science and Technology, 2020, 9, 015012.	0.9	110
116	Defect reduction in nonpolar a-plane GaN films using in situ SiNx nanomask. Applied Physics Letters, 2006, 89, 041903.	1.5	109
117	Effect of threading dislocation density on Ni N_{1-x} GaN Schottky diode I-V characteristics. Journal of Applied Physics, 2006, 100, 023709.	1.1	108
118	Structural and optical properties of GaN laterally overgrown on Si(111) by metalorganic chemical vapor deposition using an AlN buffer layer. MRS Internet Journal of Nitride Semiconductor Research, 1999, 4, 1.	1.0	107
119	High power and high efficiency green light emitting diode on free-standing semipolar (112) bulk GaN substrate. Physica Status Solidi - Rapid Research Letters, 2007, 1, 162-164.	1.2	105
120	A green-yellow emitting oxyfluoride solid solution phosphor Sr $_{2-x}$ Ba $_x$ (AlO $_4$ F) $_2$ (SiO $_5$) $_x$:Ce $^{3+}$ for thermally stable, high color rendition solid state white lighting. Journal of Materials Chemistry, 2012, 22, 18204.	6.7	105
121	Hybrid tunnel junction contacts to III N_{1-x} nitride light-emitting diodes. Applied Physics Express, 2016, 9, 022102.	1.1	105
122	Improved performance of AlGaInP red micro-light-emitting diodes with sidewall treatments. Optics Express, 2020, 28, 5787.	1.7	105
123	High-quality coalescence of laterally overgrown GaN stripes on GaN/sapphire seed layers. Applied Physics Letters, 1999, 75, 1706-1708.	1.5	104
124	Demonstration of Nonpolar GaN-Based Vertical-Cavity Surface-Emitting Lasers. Applied Physics Express, 2012, 5, 092104.	1.1	104
125	2 Gbit/s data transmission from an unfiltered laser-based phosphor-converted white lighting communication system. Optics Express, 2015, 23, 29779.	1.7	103
126	Characteristics of Indium-Gallium-Nitride Multiple-Quantum-Well Blue Laser Diodes Grown by MOCVD. MRS Internet Journal of Nitride Semiconductor Research, 1997, 2, 1.	1.0	102

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127	Optical Properties of GaAs Confined in the Pores of MCM-41. Journal of Physical Chemistry B, 1998, 102, 3341-3344.	1.2	102
128	High-Power, Low-Efficiency-Droop Semipolar ($\text{Al}_{0.2}\text{Ga}_{0.8}\text{N}$) Single-Quantum-Well Blue Light-Emitting Diodes. Applied Physics Express, 2012, 5, 062103.	1.1	102
129	The Effect of Growth Environment on the Morphological and Extended Defect Evolution in GaN Grown by Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 1998, 37, 4460-4466.	0.8	101
130	Photoelectrochemical undercut etching for fabrication of GaN microelectromechanical systems. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2001, 19, 2838.	1.6	100
131	Development of Nonpolar and Semipolar InGaN/GaN Visible Light-Emitting Diodes. MRS Bulletin, 2009, 34, 318-323.	1.7	100
132	Mechanisms of lateral epitaxial overgrowth of gallium nitride by metalorganic chemical vapor deposition. Journal of Crystal Growth, 1998, 195, 328-332.	0.7	99
133	High-Power Polarization-Engineered GaN/AlGaIn/GaN HEMTs Without Surface Passivation. IEEE Electron Device Letters, 2004, 25, 7-9.	2.2	99
134	Partial strain relaxation via misfit dislocation generation at heterointerfaces in (Al,In)GaIn epitaxial layers grown on semipolar (112 \bar{A} 2) GaN free standing substrates. Applied Physics Letters, 2009, 95, .	1.5	98
135	Influence of Si doping on characteristics of InGaIn/GaN multiple quantum wells. Applied Physics Letters, 1998, 73, 1128-1130.	1.5	97
136	Two-photon absorption study of GaN. Applied Physics Letters, 2000, 76, 439-441.	1.5	97
137	Morphological and Structural Transitions in GaN Films Grown on Sapphire by Metal-Organic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 1996, 35, L1648-L1651.	0.8	96
138	Demonstration of ultra-small ($\sim 10^{-4}\mu\text{m}$) 632 nm red InGaIn micro-LEDs with useful on-wafer external quantum efficiency ($\sim 0.2\%$) for mini-displays. Applied Physics Express, 2021, 14, 011004.	1.1	96
139	Metalorganic chemical vapor deposition growth of high optical quality and high mobility GaN. Journal of Electronic Materials, 1995, 24, 1707-1709.	1.0	95
140	Microstructure and enhanced morphology of planar nonpolar m-plane GaN grown by hydride vapor phase epitaxy. Journal of Electronic Materials, 2005, 34, 357-360.	1.0	95
141	Gallium nitride based transistors. Journal of Physics Condensed Matter, 2001, 13, 7139-7157.	0.7	94
142	Optical and structural properties of GaN nanopillar and nanostripe arrays with embedded InGaIn \cdot GaN multi-quantum wells. Journal of Applied Physics, 2006, 100, 054314.	1.1	94
143	Revealing the importance of light extraction efficiency in InGaIn/GaN microLEDs via chemical treatment and dielectric passivation. Applied Physics Letters, 2020, 116, .	1.5	94
144	Short channel AlGaIn/GaN MODFET's with 50-GHz $f_{\text{sub T}}$ and 1.7-W/mm output-power at 10 GHz. IEEE Electron Device Letters, 1997, 18, 438-440.	2.2	93

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145	Milliwatt Power Blue InGaN/GaN Light-Emitting Diodes on Semipolar GaN Templates. Japanese Journal of Applied Physics, 2005, 44, L945-L947.	0.8	93
146	High Brightness Violet InGaN/GaN Light Emitting Diodes on Semipolar $(10\bar{1}1)$ Bulk GaN Substrates. Japanese Journal of Applied Physics, 2007, 46, L129-L131.	0.8	93
147	High mobility two-dimensional electron gas in AlGaIn/GaN heterostructures grown by plasma-assisted molecular beam epitaxy. Applied Physics Letters, 1999, 74, 3528-3530.	1.5	92
148	Roughening Hexagonal Surface Morphology on Laser Lift-Off (LLO) N-Face GaN with Simple Photo-Enhanced Chemical Wet Etching. Japanese Journal of Applied Physics, 2004, 43, L637-L639.	0.8	92
149	Charge control and mobility in AlGaIn/GaN transistors: Experimental and theoretical studies. Journal of Applied Physics, 2000, 87, 7981-7987.	1.1	89
150	Ion implanted AlGaIn-GaN HEMTs with nonalloyed Ohmic contacts. IEEE Electron Device Letters, 2005, 26, 283-285.	2.2	89
151	High Brightness Blue InGaIn/GaN Light Emitting Diode on Nonpolar m-plane Bulk GaN Substrate. Japanese Journal of Applied Physics, 2007, 46, L960-L962.	0.8	89
152	Radiative and nonradiative processes in strain-free Al _x Ga _{1-x} N films studied by time-resolved photoluminescence and positron annihilation techniques. Journal of Applied Physics, 2004, 95, 2495-2504.	1.1	88
153	Accurate mobility and carrier concentration analysis for GaN. Solid State Communications, 1997, 102, 297-300.	0.9	85
154	Properties of N-polar AlGaIn/GaN heterostructures and field effect transistors grown by metalorganic chemical vapor deposition. Journal of Applied Physics, 2008, 103, .	1.1	85
155	Nonpolar III-nitride vertical-cavity surface-emitting lasers incorporating an ion implanted aperture. Applied Physics Letters, 2015, 107, .	1.5	85
156	An Efficient, Thermally Stable Cerium-Based Silicate Phosphor for Solid State White Lighting. Inorganic Chemistry, 2013, 52, 8010-8016.	1.9	84
157	Continuous-wave Operation of AlGaIn-cladding-free Nonpolar m-Plane InGaIn/GaN Laser Diodes. Japanese Journal of Applied Physics, 2007, 46, L761.	0.8	83
158	Characterization of blue-green m-plane InGaIn light emitting diodes. Applied Physics Letters, 2009, 94, 261108.	1.5	83
159	Cathodoluminescence mapping of epitaxial lateral overgrowth in gallium nitride. Applied Physics Letters, 1999, 74, 2035-2037.	1.5	82
160	AlGaIn-Cladding Free Green Semipolar GaN Based Laser Diode with a Lasing Wavelength of 506.4 nm. Applied Physics Express, 2010, 3, 011002.	1.1	82
161	Femtosecond studies of carrier dynamics in InGaIn. Applied Physics Letters, 1997, 70, 2004-2006.	1.5	81
162	High quality AlN grown on SiC by metal organic chemical vapor deposition. Applied Physics Letters, 2008, 93, .	1.5	81

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